Tolerancing of diffraction-limited Kirkpatrick-Baez synchrotron

beamline optics for EUV metrology

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Abstract: The recent interest in extreme ultraviolet (EUV) lithography has led to the

development of an array of at-wavelength metrologies implemented on synchrotron beamlines.

These beamlines commonly use Kirkpatrick-Baez systems consisting of two perpendicular,

elliptically-bent mirrors in series. To achieve high-efficiency focusing into a small spot,

unprecedented fabrication and assembly tolerance is required of these systems. Here we present a

detailed error-budget analysis and develop a set of specifications for diffraction-limited

performance for the Kirkpatrick-Baez optic operating on the EUV interferometry beamline at

Lawrence Berkeley National Laboratory's Advanced Light Source. The specifications are based

on CODE V modeling tools developed explicitly for these optical systems. Although developed

for one particular system, the alignment sensitivities presented here are relevant to Kirkpatrick-

Baez system designs in general.

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	M5	M6
Tilt	±0.0046°	±0.0054°
Roll	±0.025°	±0.046°
Yaw	±0.44°	±0.86°

Table 1. Rotation error tolerances for M5 and M6. Rotations are made about the centers of the mirrors. The axes are defined as shown in Figure 4. Tolerances are defined as those errors that cause a doubling in the width of the point spread function.

Note: Printed at full width of 35 picas.

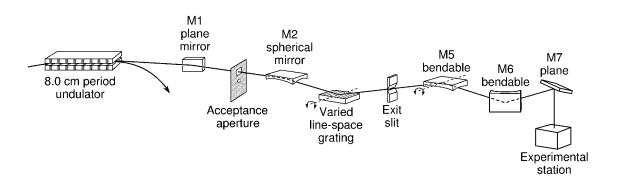


Fig. 1. Schematic of the EUV interferometry beamline at the Advanced Light Source synchrotron radiation facility at Lawrence Berkeley National Laboratory. This beamline produces a demagnified image of the undulator source at the focal plane of the K-B, corresponding to the entrance plane of the experimental station.